

Datasheet

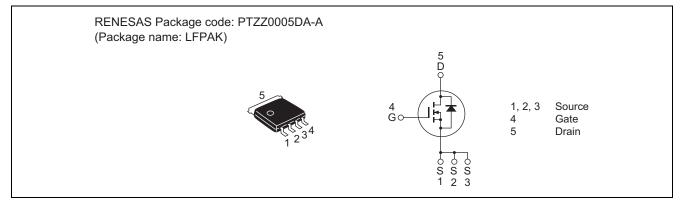
100V, 23A, 17m Ω max. Silicon N Channel Power MOS FET Power Switching

R07DS1058EJ0200 (Previous: REJ03G1887-0100) Rev.2.00 Apr 11, 2013

Features

- High speed switching
- Low drive current
- Low on-resistance
 - $R_{DS(on)} = 13 \text{ m}\Omega \text{ typ.}$ (at $V_{GS} = 10 \text{ V}$)
- Pb-free
- Halogen-free
- High density mounting

Outline



Absolute Maximum Ratings

| | | | $(Ta = 25^{\circ}C)$ |
|--|--------------------------------|-------------|----------------------|
| ltem | Symbol | Ratings | Unit |
| Drain to source voltage | V _{DSS} | 100 | V |
| Gate to source voltage | V _{GSS} | ±20 | V |
| Drain current | ID | 23 | A |
| Drain peak current | Note1 I _{D(pulse)} | 92 | A |
| Body-drain diode reverse drain current | I _{DR} | 23 | A |
| Avalanche current | I _{AP} Note 2 | 23 | A |
| Avalanche energy | E _{AS} Note 2 | 5.3 | mJ |
| Channel dissipation | Pch Note3 | 60 | W |
| Channel to Case Thermal Resistance | θch-C | 2.08 | °C/W |
| Channel temperature | Tch | 150 | ٥C |
| Storage temperature | Tstg | -55 to +150 | ٥C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at L=10uH, Tch = 25° C, Rg $\geq 50 \Omega$

3. Tc = 25°C



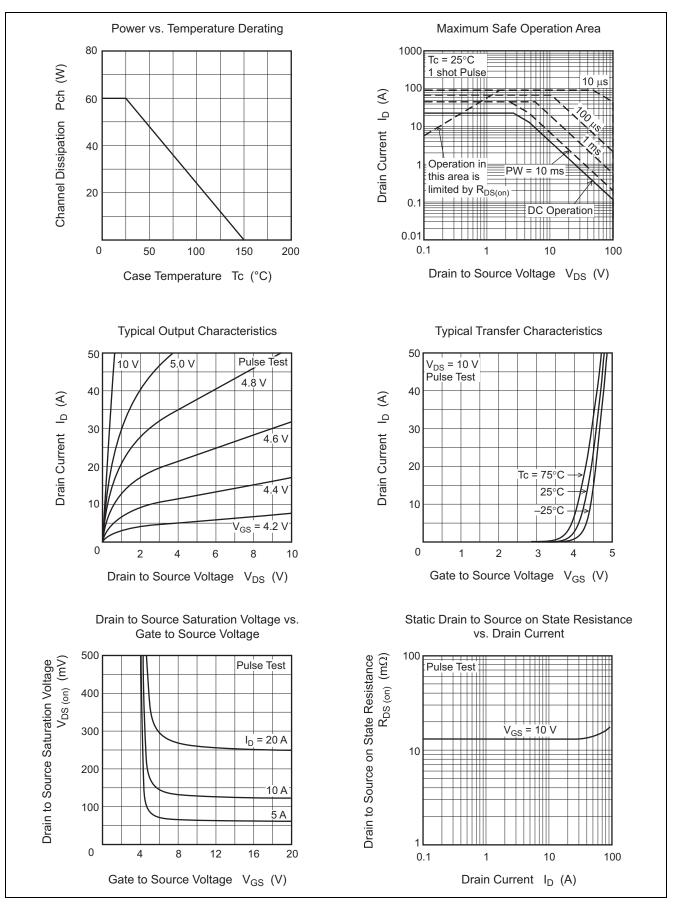
Electrical Characteristics

| | | | | | | $(Ta = 25^{\circ}C)$ |
|--|----------------------|-----|------|------|------|---|
| Item | Symbol | Min | Тур | Max | Unit | Test Conditions |
| Drain to source breakdown voltage | V _{(BR)DSS} | 100 | — | | V | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ |
| Gate to source leak current | I _{GSS} | _ | — | ±0.1 | μA | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ |
| Zero gate voltage drain current | I _{DSS} | _ | — | 1 | μA | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$ |
| Gate to source cutoff voltage | V _{GS(off)} | 2.0 | — | 4.0 | V | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 13 | 17 | mΩ | $I_D = 11.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$ |
| Forward transfer admittance | y _{fs} | _ | 37 | _ | S | $I_D = 11.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$ |
| Input capacitance | Ciss | _ | 2550 | _ | pF | $V_{DS} = 10 V, V_{GS} = 0 V,$ |
| Output capacitance | Coss | _ | 420 | _ | pF | f = 1 MHz |
| Reverse transfer capacitance | Crss | _ | 100 | _ | pF | |
| Gate Resistance | Rg | _ | 0.5 | _ | Ω | |
| Total gate charge | Qg | _ | 35 | _ | nC | $V_{DD} = 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$ |
| Gate to source charge | Qgs | _ | 11 | _ | nC | I _D = 23 A |
| Gate to drain charge | Qgd | _ | 7.0 | _ | nC | |
| Turn-on delay time | t _{d(on)} | _ | 14 | _ | ns | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11.5 \text{ A},$ |
| Rise time | tr | _ | 4.2 | _ | ns | $\label{eq:VDD} \begin{array}{l} V_{DD} \cong 30 \ V, \ R_{L} = 2.6 \ \Omega, \\ Rg = 4.7 \ \Omega \end{array}$ |
| Turn-off delay time | t _{d(off)} | _ | 34 | _ | ns | |
| Fall time | t _f | _ | 6.2 | _ | ns | |
| Body-drain diode forward voltage | V _{DF} | | 0.8 | 1.1 | V | $I_F = 23 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$ |
| Body-drain diode reverse recovery time | t _{rr} | _ | 50 | | ns | I _F = 23 A, V _{GS} = 0 V |
| | | | | | | di _F / dt = 100 A/ μs |

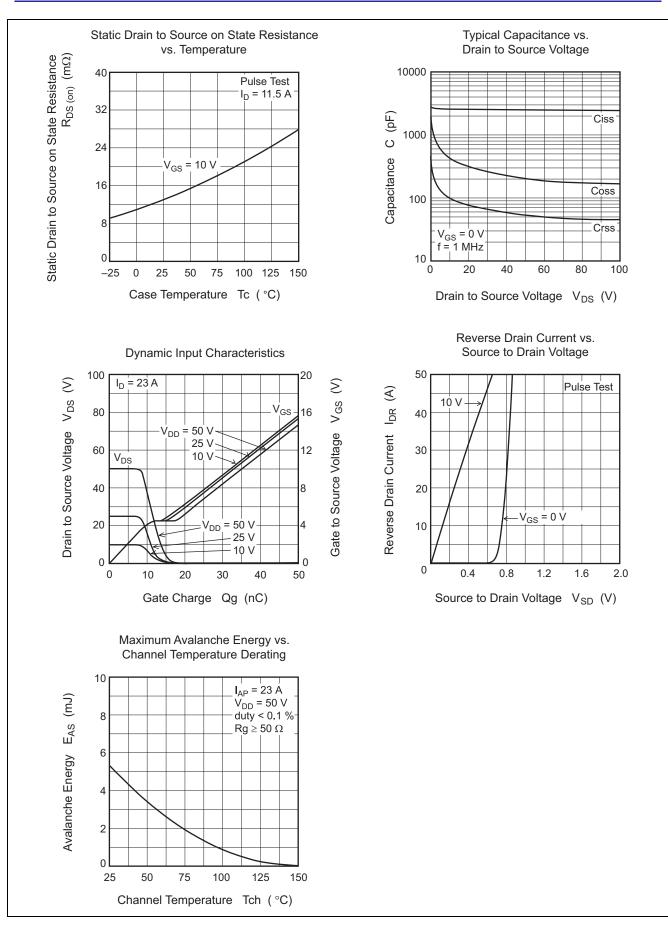
Notes: 4. Pulse test

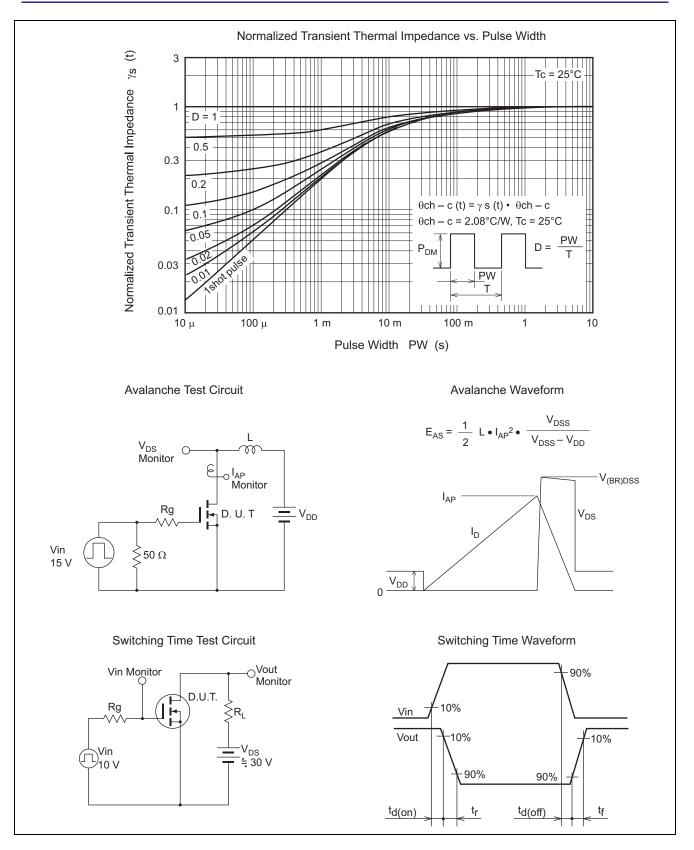


Main Characteristics

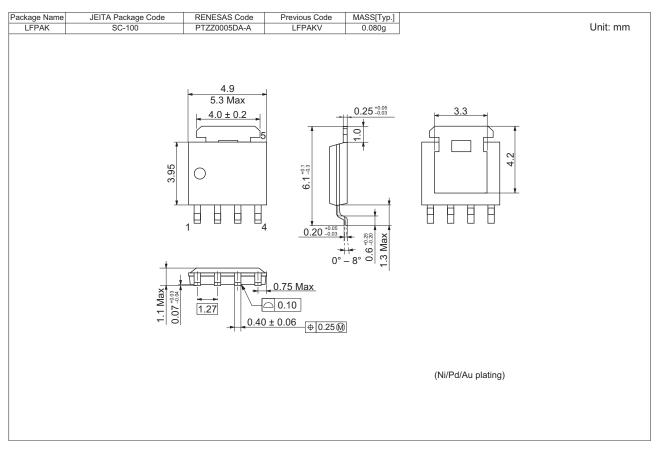








Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK1055DPB-00-J5 | 2500 pcs | Taping |



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